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- ¶ IGBT CHIP(Trench+Field Stop technology)

- ¶ $V_{CE(sat)}$ with positive temperature coefficient

- ¶ High short circuit capability

- ¶ Fast switching and short tail current

- ¶ Free wheeling diodes with fast and soft reverse recovery

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- ¶ Motion/servo control

- ¶ UPS systems

T_{Jop}

Unit

V

Nm

Nm

g

$I_c(A)$

$V_{GE} \text{ \AA V \AA}$

Figure 3. Typical Transfer characteristics IGBT-inverter

$E_{on}E_{off}(mJ)$

$R_g \text{ \AA \AA}$

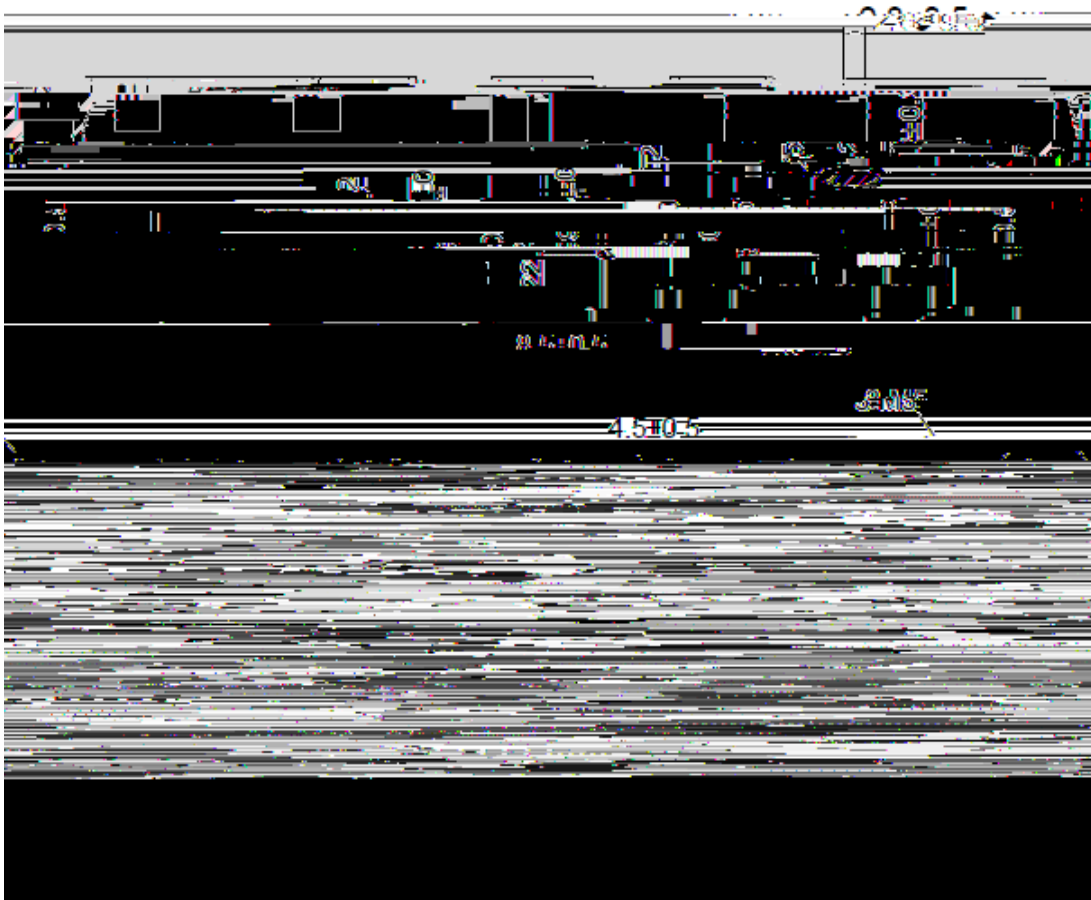
Figure 4. Switching Energy vs Gate Resistor IGBT-inverter

Figure 9. Diode Forward Characteristics Diode -inverter

Figure 10. Switching Energy vs Gate Resistor Diode -
inverter

nJ)

Figure 13. Circuit Diagram



Dimensions in (mm)
Figure 14. Package Outline